

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In the Specification

Please amend the title on Page 1, line 1, with the following.

5 RANDOM ACCESS MEMORY CELL HAVING REDUCED CURRENT LEAKAGE AND  
HAVING A PASS TRANSISTOR CONTROL GATE FORMED IN A TRENCH

Please replace the paragraph beginning on Page 1, line 4, with the following.

10 This application is a continuation of U.S. Patent Application Serial No. 09/546,747, filed April 11, 2000, which is a divisional of U.S. Patent No. 6,064,589 filed May 5, 1998, which is based on provisional application number 60/073,349 filed on February 2, 1998.